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FILING DATE FIRST NAMED INVENTOR ATTORNEY DOCKET NO. CONFIRMATION NO APPLICATION NO. 09 651,790 08 30 2000 Pary Baluswamy CF 027 PROV 7590 06 19 2002 Samuel E Webb EXAMINER Trask Britt PIZARRO CRESPO, MARCOS D

P O Box 2550 Salt Lake City, UT 84110

PAPER NUMBER ART UNIT

2814

DATE MAILED: 06/19/2002

Please find below and/or attached an Office communication concerning this application or proceeding.

•		Application No.	Applicant(s)	μų
Office Action Summary		09/651,790	BALUSWAMY ET	AL.
		Examiner	Art Unit	
		Marcos D. Pizarro-Crespo	2814	
Period fo	The MAILING DATE of this communication app or Reply	ears on the cover sheet with the o	correspondence add	iress
A SH THE - Exte after - If the - If NC - Failu	ORTENED STATUTORY PERIOD FOR REPLY MAILING DATE OF THIS COMMUNICATION. nsions of time may be available under the provisions of 37 CFR 1.13 SIX (6) MONTHS from the mailing date of this communication. e period for reply specified above is less than thirty (30) days, a reply operiod for reply is specified above, the maximum statutory period were to reply within the set or extended period for reply will, by statute, reply received by the Office later than three months after the mailing	of6(a). In no event, however, may a reply be tirm within the statutory minimum of thirty (30) day ill apply and will expire SIX (6) MONTHS from cause the application to become ABANDONE	mely filed ys will be considered timely. In the mailing date of this core ED (35 U.S.C. § 133).	
	ed patent term adjustment. See 37 CFR 1.704(b).	date of this communication, even if timely med	a, may reduce any	
1)	Responsive to communication(s) filed on 24 M	<u>1ay 2002</u> .		
2a)⊡	This action is FINAL . 2b) Thi	s action is non-final.		
3)∏ Dispositi	Since this application is in condition for allowa closed in accordance with the practice under <i>l</i> ion of Claims			e merits is
4)	Claim(s) $1-21$ is/are pending in the application			
	4a) Of the above claim(s) 1-15 is/are withdrawn	from consideration.		
5)	Claim(s) is/are allowed.			
6)⊡	Claim(s) <u>16-21</u> h/are rejected.			
7)	Claim(s) is/are objected to.			
•	Claim(s) <u>1-21</u> are subject to restriction and/or e	lection requirement.		
· · · —	The specification is objected to by the Examiner			
	The drawing(s) filed on is/are: a)□ accep		miner.	
	Applicant may not request that any objection to the			
11)[-]	The proposed drawing correction filed on <u>24 Ma</u>	<u>y 2002</u> is: a)⊠ approved b)⊡ d	isapproved by the E	xaminer.
	If approved, corrected drawings are required in rep	ly to this Office action.		
12) 🗌 🗆	The oath or declaration is objected to by the Exa	iminer.		
Priority u	ınder 35 U.S.C. §§ 119 and 120			
13)	Acknowledgment is made of a claim for foreign	priority under 35 U.S.C. § 119(a	ı)-(d) or (f).	
a)[☐ All b) ☐ Some * c) ☐ None of:			
	1. Certified copies of the priority documents	have been received.		
	2. Certified copies of the priority documents	have been received in Applicati	on No	
* S	3. Copies of the certified copies of the priori application from the International Burdee the attached detailed Office action for a list of	eau (PCT Rule 17.2(a)).		itage
 Attachment	so Nico voltaja ovijeno je o klad i okali od kole o objektiva i ovijenska i (s)	, , , , , , , , , , , , , , , , , , ,	at I	
1) ⊠ N≃ ce	e of References Cited (PTO-892)	4- Interview Summary	r (PTO-413) Paper Nors	ì
	and the great production of the production of the control of the c		And the property of	

Application/Control Number: 09/651,790 (Final Rejection)

Art Unit: 2814

Attorney's Docket Number: 4307 US (99-1193)

Filing Date: 8/20/2000

Claimed Foreign Priority Date: none

Applicant(s): Baluswamy et al.

Examiner: Marcos D. Pizarro-Crespo

DETAILED ACTION

This Office action responds to the amendment (paper no. 15) filed on 5/24/2002.

Acknowledgment

1. The amendment (paper no. 15) filed on 5/24/2002 in response to the Office action (paper no. 12) mailed on 2/26/2002 has been entered. The present Office action (paper no. 16) is made with all the suggested amendments being fully considered. Accordingly, pending in this Office action are claims 1-21.

Drawings

2. The proposed drawing corrections and/or the proposed substitute sheets of drawings, filed on 1/3/2001 and on 5/24/2002 have been approved. A proper drawing correction or corrected drawings are required in reply to the Office action to avoid **ABANDONMENT** of the application. The correction to the drawings will not be held in abeyance.

Claim Rejections - 35 USC § 102

Page 2

Art Unit: 2814

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

- 4. Claims 16-20 are rejected under 35 U.S.C. 102(b) as being anticipated by Deguchi (JP 62-18714).
- 5. Deguchi shows (see, e.g., fig. 1, abstract) all aspects of the instant invention including a method to form an overlay target including a series of raised lines, the method comprising:
 - providing a substrate 10
 - depositing a resist layer 15 over the substrate 10
 - patterning the resist layer 15 to include a pattern defining the overlay target (abstract)
 - retching the substrate 10 to form the overlay target
- 6. Regarding claim 17, Deguchi shows (abstract) that the substrate comprises a semiconductor substrate.
- 7. Regarding claim 18, Deguchi deposits the resist layer **15** directly over the semiconductor substrate **10** (see, e.g., fig. 1).
- 8. Regarding claim 19. Deguchi shows that a material layer **14** may be deposited over the top surface of the semiconductor substrate **10** (see, *e.g.*, fig. 4).
- 9. Regarding claim 20, Deguchi shows that the resist layer **15** may be deposited over the material layer **14** so that the step of etching the substrate **10** comprises etching

Art Unit: 2814

- 11. Kinoshita shows (see, *e.g.*, fig. 3, abstract) all aspects of the instant invention including a method to form an overlay target including a series of raised lines, the method comprising:
 - providing a substrate 1
 - depositing a resist layer 22, 25 over the substrate 1
 - patterning the resist layer 22, 25 to include a pattern 23, 24 defining the overlay target
 - etching the substrate 1 to form the overlay target 4, 5, 7

Claim Rejections - 35 USC § 103

- 12. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 13. This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to

Application/Control Number: 09/651,790 (Final Rejection)

Art Unit: 2814

14. Claim 21 is rejected under 35 U.S.C. 103(a) as being unpatentable over

Page 5

Kinoshita in view of Xu (US 5908319).

15. Regarding claim 21, Kinoshita shows most aspects of the instant invention (see

paragraph 11 above), except for the substrate etching step comprising wet etching the

substrate 1 to form the overlay target 4, 5, 7. Kinoshita differently teaches the use of

plasma etching.

Xu, on the other hand, teaches that wet etching and plasma etching are known

etching techniques that are conventionally used in the fabrication of integrated circuits

(col.1/ll.10,11,21,25). As expressed by Xu, etching is typically performed with either wet

etching or plasma etching (col.1/II.21-24).

It would have been obvious to a person having ordinary skill in the art at the time

of the invention to have a wet-etching step instead of the plasma-etching step in

Kinoshita's process, as taught by Xu, since etching is typically performed in the

semiconductor industry by either plasma-etching or wet-etching.

Response to Arguments

16. The applicants argue:

Deguchi does not disclose overlay targets with a series of raised lines nor does it teach a semiconductor substrate selected from the group consisting of silicon, gallium and sapphire substrates.

The examiner responds:

Contrary to applicants' statements, Dequchi clearly shows (see, e.g., attached

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translation provided by the applicants in paper no. 14)

Art Unit: 2814

Conclusion

- 17. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).
- 18. A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.
- 19. Papers related to this application may be submitted directly to Art Unit 2814 by facsimile transmission. Papers should be faxed to Art Unit 2814 via the Art Unit 2814 Fax Center located in Crystal Plaza 4, room 3C23. The faxing of such papers must conform to the notice published in the Official Gazette, 1096 OG 30 (15 November 1989). The Art Unit 2814 Fax Center number is (703) 308-7722 or -7724. The Art Unit 2814 Fax Center is to be used only for papers related to Art Unit 2814 applications.
- 20 Any inquiry concerning this communication or earlier communications from the

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between the hours of 9.00 AM to 7.30 PM (Eastern Standard Time) Monday through

Thursday or by e-mail via Marcos Pizarro@uspto gov. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Olik Chaudhuri, can be reached on (703) 306-2794.

- 21. Any inquiry of a general nature or relating to the status of this application should be directed to the **Group 2800 Receptionist** at **(703) 308-0956**.
- 22. The following list is the Examiner's field of search for the present Office Action:

Field of Search	Date
U.S. Class / Subclass(es): 257 /797 438 /401, 462, 704, 706, 709-711, 719, 745, 783, 975	6/12/2002
Other Documentation:	
Electronic Database(s): EAST (USPAT, EPO, JPO)	6/12/2002

Marcos D. Pizarro-Crespo

Patent Examiner Art Unit 2814

特開昭62-18714 (4)

成できる。

本発明は、以上の実施例に限定されることなく、公知のドライエッチング法を適用すれば種々の材料の表面状態を光学的に反射率の低い酸小な凹凸形状になし得るため、その応用範囲は極めて広い。

[発明の効果]

以上説明したように本発明によれば、被露光 要板に設けるアライメントマークの照明光に対 するコントラストを大幅に改善でき、しかも、 その形成方法が極めて簡便でかつ運めて高い歩 留りが得られる利点を有する。

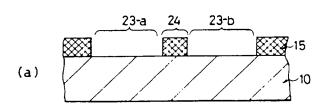
4.図面の簡単な説明

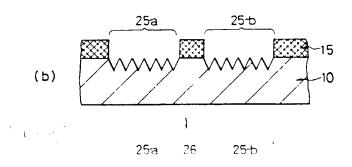
第1図は本発明の一実施例を示す断面図、第2図は本発明の他の実施例を示す断面図、第3図はアライメントマークの検出原理を説明する図、第4図は従来のアライメントマークの形成方法を説明する断面図である。

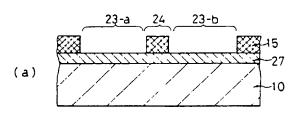
1 …マスクのアライメントマーク、 2 … 高反射部、 3 … 透逸部、 4 … ウェハのアライメント

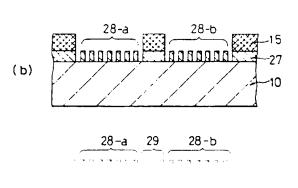
マーク、 5 … 高反射部、 6 … 低反射部、 7 … 照 明光、8…マスクマークからの反射光、9…ウ ェハマークからの反射光、10…基板、11… マスクマークの検出信号、12…ウェハマーク の検出信号、13…パックグランド、14…マ スク材雕、15…レジスト、16…ラインアン ドスペースレジストバタン、11…直線レジス トパタン、18…ラインアンドスペースマスク 材層バタン、19… 直線マスク材屑バタン、 20…円弧状断面を有する多数の微小窪みの配 列からなる領域、21…円弧状パタン、22… 平滑面、28…アライメントマークパタンのレ ジストのない部分、24…アライメントマーク パタンのレジストパタン、25… 敬小な四角錐 状の処起群、26…レジストパタン下部、27 ··· M o 膜、 2 8 ··· 像 小 な 柱 状 結 晶 が 林 立 し た 凹 凸群、29…レジストパタン下部。

出願人代理人 弁理士 鈴 江 武 彦









第 1 図

第 2 図